
INDEX

A

- ADC load-board design, 436–439
- Admittance parameters, 272–273
- All-pass functions, 299
- Analytical modeling methods
 - cavity resonator, network representation, 135–138
 - cavity resonator method, 133–135
 - Green's function, 133–138
 - rectangular planes, 133–138
- Antiresonance
 - frequencies, board planes, 41–42
 - planes, modeling, 86–88
- Apertures, coupling multiple plane pairs, 158–169

B

- BEMP (Broadband Efficient Macromodeling Program), 258–266, 458
- Board planes
 - antiresonance frequencies, 41–42
 - considerations, 41–42
 - description, 37
 - electromagnetic resonant cavities, 38–40
 - impedance, 40–41
 - plane bounce, 40
 - plane pairs, 37–39
 - resonance, 39–40
 - resonance frequencies, 41–42
 - role of, 39
- Buck switching regulator, 26–27
- Bulk decoupling capacitors, 34
- Bypass capacitors. *See also* Capacitors;
Decoupling capacitors.
 - bulk decoupling, 34
 - ceramic, 36–38
 - description, 28–29
 - ESL (equivalent series inductance), 30–31
 - ESR (equivalent series resistance), 29–31
 - examples, 33, 34–35

- frequency response, 30–31
- impedance, 30–31
- impedance peaks, 33
- inductance
 - effect on performance, 29–33
 - ESL (equivalent series inductance), 30–31
 - ESR (equivalent series resistance), 29–31
 - ground planes, 32–33
 - lowering, limiting factor, 32
 - magnetic flux, 31–32
 - versus* pad/via layout, 32–33
 - pul (per-unit-length), 33
 - time-varying current, 29–30
 - voltage planes, 32–33
- mid-frequency SMDs, 36–37
- NOP capacitors, 36–37
- overall loop inductance, 32
- performance factors, 29–34
- Q (quality) factor, 35–36
- SMDs (surface mount devices), 29
- usefulness of, 35–36
- X5R capacitors, 36–37
- X7R capacitors, 36–37
- Y5V capacitors, 36–37

C

- Capacitance, calculating for planes, 85–86
- Capacitors
 - bypassing VRMs. *See* Bypass capacitors;
Decoupling capacitors.
 - ceramic, 36–38
 - current relationship, 17–19
 - decoupling. *See* Decoupling capacitors.
 - embedded. *See* Embedded decoupling capacitors.
- Causal SFGs, 302–303
- Causality, SFGs, 296
- Cavity resonator method, 133–135, 337–340
- Cavity resonator model, network representation, 135–138
- Ceramic capacitors, 36–38

Chip package analysis. *See* High-speed differential signaling; High-speed server analysis; ICs (integrated circuits), package analysis.

CMOS MOSFET technology, 1–3

Coaxial cables, 72–73

Complex conjugate poles, 270–272

Computer-backed coplanar waveguide (CPW), 205–207

Conducted emissions, controlling, 28

Conductor losses, 111–113

Conductors, coupling multiple plane pairs, 154–158

Control loop optimization, 28

Convolution

- direct, 285–287
- fast convolution methods, 307–312
- integration in a circuit solver, 283–288
- recursive, 287–288

Core circuits, 10–13. *See also* I/O circuits.

Core PDN noise

- measurement, 336–337
- model-to-hardware correlation, 337–340
- system-level measurement, 340–345

Coupling multiple plane pairs

- M-FDM (multilayered finite-difference method), 159–169
- through apertures, 158–169
- through conductors, 154–158
- through vias, 141–154

CPW (computer-backed coplanar waveguide), 205–207

CPW mode, 205–207

Curve fitting, 257–258

D

DC-DC converters, 25–28

Debye model, 106–111, 386–391

Decoupling capacitors. *See also* Bypass capacitors; Capacitors.

- bulk decoupling, 34
- ceramic, 36–38
- current relationship, 17–19
- description, 28–29
- effectiveness, measuring. *See* High-frequency measurements.
- embedded. *See* Embedded decoupling capacitors.
- ESL (equivalent series inductance), 30–31
- ESR (equivalent series resistance), 29–31
- examples, 33, 34–35
- frequency response, 30–31
- impedance, 30–31
- impedance peaks, 33
- inductance
 - effect on performance, 29–33
 - ESL (equivalent series inductance), 30–31
 - ESR (equivalent series resistance), 29–31
 - ground planes, 32–33
 - lowering, limiting factor, 32
 - magnetic flux, 31–32
 - versus* pad/via layout, 32–33
 - pul (per-unit-length), 33
 - time-varying current, 29–30
 - voltage planes, 32–33
- mid-frequency SMDs, 36–37
- NOP capacitors, 36–37
- on-chip, 43

overall loop inductance, 32

performance factors, 29–34

Q (quality) factor, 35–36

SMDs (surface mount devices), 29

usefulness of, 35–36

uses for, 7

X5R capacitors, 36–37

X7R capacitors, 36–37

Y5V capacitors, 36–37

Delay extraction from frequency response, 300–302

Dielectrics

- constant, extracting. *See* Dielectrics, extracting material properties.
- extracting material properties
 - causal model development, 386–391
 - corner-to-corner plane probing, 378–386
 - introduction, 372–373
 - problem definition, 373–378
- loss tangent, extracting. *See* Dielectrics, extracting material properties.
- noise coupling reduction, 231–233

Digital signal spectrum, 454–457

Digital systems issues, 439–442

Digital/RF integration, 434–436

Direct convolution, 285–287

Discrete cosine transform, 126–128

Discretization-based plane modeling

- FDM (finite-difference method)
 - description, 117–123
 - discrete cosine transform, 126–128
 - five-point approximation, *versus* nine-point, 124–126
 - rapid solver for rectangular planes, 126–128
 - T-unit cell *versus* X-unit cell, 123–124
- FDTD (finite-difference time-domain) method, 128–132
- FEM (finite element method), 132–133
- rectangular planes, rapid solver, 126–128

Dispersion-diagram analysis

- introduction, 420–421
- one-dimensional EBG structures, 421–422
- two-dimensional EBG structures, 422–424

Distributed circuit-based modeling. *See also* Lumped modeling.

- frequency-dependent unit cell elements
 - conductor losses, 111–113
 - Debye model, 106–111
 - description, 104–106
 - Kramers–Kronig relationship, 106–111
 - loss tangents, calculating, 107–108
 - skin effect, 111–113
 - substrate losses, 106–111
- gaps in planes, 113–117
- TMM (transmission matrix method), 97–104
- transmission lines, 94–97

Drains, 2–3

Drivers. *See* Inverters.

E

EBG (electromagnetic bandgap) structures

- ADC load-board design, 436–439
- digital systems issues, 439–442

- digital/RF integration, 434–436
 - dispersion-diagram analysis
 - introduction, 420–421
 - one-dimensional EBG structures, 421–422
 - two-dimensional EBG structures, 422–424
 - EBG structure response, 417–420
 - introduction, 415–416
 - M-FDM modifications
 - fringe fields, 424–427
 - gap fields, 427–430
 - scalable design for power plane isolation, 430–434
 - theory, 416–417
 - Eigenvalue method, 246–249
 - Electromagnetic resonant cavities, 38–40
 - Embedded decoupling capacitors. *See also* Capacitors; Decoupling capacitors.
 - embedded planar capacitors
 - FSB (front-side bus), 405, 410–411
 - introduction, 404–405
 - planar capacitors, 405–407
 - SSN, and jitter and voltage margin, 410–415
 - test vehicle, 407–410
 - integrating into IBM packages, 400–404
 - introduction, 392–394
 - purpose of, 395
 - thick-film capacitor arrays, designing, 395–400
 - thin- or thick-film capacitors, 394–395
 - Embedded planar capacitors. *See also* Capacitors; Decoupling capacitors; Embedded decoupling capacitors.
 - FSB (front-side bus), 405, 410–411
 - introduction, 404–405
 - planar capacitors, 405–407
 - SSN, and jitter and voltage margin, 410–415
 - test vehicle, 407–410
 - ESL (equivalent series inductance), 30–31
 - ESR (equivalent series resistance), 29–31
 - Eye diagram, simulating, 368–372
- F**
- Fast convolution methods, 307–312
 - FDM (finite-difference method)
 - description, 117–123
 - discrete cosine transform, 126–128
 - five-point approximation, *versus* nine-point, 124–126
 - rapid solver for rectangular planes, 126–128
 - T-unit cell *versus* X-unit cell, 123–124
 - FDTD (finite-difference time-domain) method, 128–132
 - FEM (finite element method), 132–133
 - FFT (fast Fourier transform), 304–305
 - Five-point approximation, *versus* nine-point, 124–126
 - Four-element model, 26–27
 - Frequency domain analysis
 - discretization-based plane models. *See* FDM (finite-difference method).
 - microstrip-to-stripline via transition, 228–231
 - MNA (modified nodal analysis), 318–320
 - noise coupling reduction with thin dielectrics, 231–233
 - PDN analysis
 - cavity response, 53–55
 - distributed analysis, 55–60
 - introduction, 45–48
 - plane inductance, calculating at low frequencies, 52–56
 - single-node analysis, 48–55
 - target impedance, meeting, 53–55, 59–60
 - PDN design, 20–21
 - plane behavior, 84–86
 - stripline, between power and ground plane, 226–228
 - Frequency response
 - bypass capacitors, 30–31
 - ceramic capacitors, 38
 - decoupling capacitors, 30–31
 - extracting from planes. *See* Plane modeling.
 - modeling. *See* Rational functions; SFGs (signal flow graphs).
 - Frequency-dependent unit cell elements
 - conductor losses, 111–113
 - Debye model, 106–111
 - description, 104–106
 - Kramers–Kronig relationship, 106–111
 - loss tangents, calculating, 107–108
 - skin effect, 111–113
 - substrate losses, 106–111
 - Frequency-voltage relationship, 5–7
 - Fringe fields, 424–427
 - FSB (front-side bus), 405, 410–411
 - Future of power integrity modeling, 443–445
- G**
- Gap fields, 427–430
 - Gaps in planes, modeling, 113–117
 - Gate (transistor) delays, 5
 - Gates, 2–3
 - Gibbs phenomenon, 305–307
 - Green's function, 133–138
 - Ground planes
 - inductance, 32–33
 - resonance, 39–40
- H**
- Hamiltonian matrix method
 - admittance parameters, 272–273
 - complex conjugate poles, 270–272
 - IdEM (Identification of Electrical Macromodels), 282–283
 - impedance parameters, 272–273
 - overview, 266–272
 - perturbation of matrices, 274–283
 - real poles, 268–270
 - scattering parameters, 273–276
 - High-frequency measurements
 - description, 65–66
 - examples, 69
 - impedance, 66–67, 70–71
 - probe inductance, eliminating, 70–71
 - self-impedance, 68–69
 - transfer-impedance, 70
 - High-speed differential signaling
 - introduction, 349–350
 - master/slave islands, modeling, 358–360
 - modal decomposition, 361–364

- noise simulation, 361–364
 - plane modeling, 352–358
 - rational function modeling, 361
 - test vehicle, 350–352
 - High-speed server analysis
 - core PDN noise
 - measurement, 336–337
 - model-to-hardware correlation, 337–340
 - system-level measurement, 340–345
 - introduction, 334–335
 - I/O PDN noise
 - description, 345
 - model-to-hardware correlation, 345–346
 - system-level model and measurement, 346–349
 - HyperBGA package, causal simulation, 368–372
- I**
- IBIS (I/O buffer information specification), 180–184
 - ICs (integrated circuits). *See also* Transistors.
 - external internal communication. *See* I/O circuits.
 - internal communication. *See* Core circuits.
 - package analysis
 - HyperBGA package, causal simulation, 368–372
 - introduction, 365–366
 - multilayered package, with M-FDM, 366–367
 - power delivery, importance of, 5–6
 - types of, 10. *See also specific types.*
 - IdEM (Identification of Electrical Macromodels), 282–283
 - Impedance
 - board planes, 40–41
 - bypass capacitors, 30–31
 - decoupling capacitors, 30–31
 - high-frequency measurements, 66–67, 70–71
 - measuring
 - by eliminating probe inductance, 70–71
 - self-impedance, 68–69
 - transfer impedance, 70
 - VNA (vector network analyzer), 66–67, 336–337
 - parameters, 272–273
 - peaks, 33
 - self, 46–47, 68–69
 - transfer, 46, 70
 - Inductance
 - bypass capacitors
 - effect on performance, 29–33
 - ESL (equivalent series inductance), 30–31
 - ESR (equivalent series resistance), 29–31
 - ground planes, 32–33
 - lowering, limiting factor, 32
 - magnetic flux, 31–32
 - versus pad/via layout, 32–33
 - pul (per-unit-length), 33
 - time-varying current, 29–30
 - voltage planes, 32–33
 - decoupling capacitors
 - effect on performance, 29–33
 - ESL (equivalent series inductance), 30–31
 - ESR (equivalent series resistance), 29–31
 - ground planes, 32–33
 - lowering, limiting factor, 32
 - magnetic flux, 31–32
 - versus pad/via layout, 32–33
 - pul (per-unit-length), 33
 - time-varying current, 29–30
 - voltage planes, 32–33
 - lowering, limiting factor, 32
 - overall loop inductance, 32
 - planes, calculating, 85–86
 - probe, eliminating, 70–71
 - Inductance matrices, extracting, 90–94
 - Inhomogeneous medium, 201–205
 - Integrated circuits (ICs). *See* ICs (integrated circuits).
 - Integration in a circuit solver
 - convolution, 283–288
 - direct convolution, 285–287
 - recursive convolution, 287–288
 - Spice subcircuit, 288–291
 - Interconnect (wire) delays, 5
 - Interconnections, separating from planes. *See* Modal decomposition.
 - Interpolation schemes
 - eigenvalue method, 246–249
 - pole identification, 249–251
 - residue identification, 251
 - vector fitting method, 249–251
 - Inverse Z-transform, 304–305
 - Inverters, 2–3
 - I/O buffer information specification (IBIS), 180–184
 - I/O circuits. *See also* Core circuits.
 - delay, due to SSN, 15–16
 - description, 14
 - examples, 14–15
 - I/O PDN noise
 - description, 345
 - model-to-hardware correlation, 345–346
 - system-level model and measurement, 346–349
- J**
- Jitter
 - definition, 17
 - effects of, 17
 - figure, 19
 - SSN effects, 410–415
- K**
- Kaiser window, 305–307
 - Kramers–Kronig relationship, 106–111, 386–391
- L**
- Loss tangents, calculating, 107–108
 - Lumped modeling, partial inductances, 89–94. *See also* Distributed circuit-based modeling.
- M**
- Macromodeling
 - combined with TMM. *See* High-speed differential signaling.
 - eigenvalue method, 246–249
 - pole identification, 249–251

- residue identification, 251
 - vector fitting method, 249–251
 - Magnetic flux, 31–32
 - M-FDM (multilayered finite-difference method)
 - coupling multiple plane pairs, 159–169
 - incorporating transmission lines
 - application. *See* ICs (integrated circuits), package analysis.
 - complex board design, 236–238
 - overview, 233–236
 - modifications
 - fringe fields, 424–427
 - gap fields, 427–430
 - Microprocessors. *See also* Transistors.
 - description, 5–6
 - frequency-voltage relationship, 5–7
 - gate (transistor) delays, 5
 - interconnect (wire) delays, 5
 - power delivery, importance of, 5–6
 - speed limitations, 5
 - Microstrip configuration, 186–189
 - Microstrip mode, configuring, 186–189
 - Microstrip-to-stripline via transition, 228–231
 - Minimum phase, 296–299
 - MNA (modified nodal analysis)
 - description, 317–318
 - frequency domain, 318–320
 - S-parameters, 322–327
 - time domain, 320–322
 - Modal decomposition. *See also* Time-domain simulation.
 - definition, 185–186
 - high-speed differential signaling, 361–364
 - microstrip configuration, 186–189
 - MTL (multiconductor transmission line) theory, 185–186
 - overview, 185–186, 189
 - plane bounce
 - definition, 185
 - perforated power/ground plane, 198
 - from return currents, 209–217
 - split planes, 223–226
 - via transitions, 220
 - plane pairs, 185
 - stripline configuration
 - alternate modeling method, 196–200
 - continuous reference planes without holes, 196–200
 - CPW (computer-backed coplanar waveguide), 205–207
 - CPW mode, 205–207
 - inhomogeneous medium, 201–205
 - modeling as an MTL, 192–196
 - MTL equations, 189–192
 - overview, 189
 - parallel-plate mode, 205–207
 - perforated reference plane with a hole, 200
 - stripline, alternate modeling method, 196–200
 - stripline, modeling as an MTL, 192–196
 - summary of, 207–209
 - TEM (transverse electromagnetic) waves, 185
 - Modal decomposition, SSN. *See also* Time-domain simulation.
 - definition, 185–186
 - microstrip configuration, 186–189
 - MTL (multiconductor transmission line) theory, 185–186
 - overview, 185–186, 189
 - plane bounce
 - definition, 185
 - perforated power/ground plane, 198
 - from return currents, 209–217
 - split planes, 223–226
 - via transitions, 220
 - plane pairs, 185
 - stripline configuration
 - alternate modeling method, 196–200
 - continuous reference planes without holes, 196–200
 - CPW (computer-backed coplanar waveguide), 205–207
 - CPW mode, 205–207
 - inhomogeneous medium, 201–205
 - modeling as an MTL, 192–196
 - MTL equations, 189–192
 - overview, 189
 - parallel-plate mode, 205–207
 - perforated reference plane with a hole, 200
 - stripline, alternate modeling method, 196–200
 - stripline, modeling as an MTL, 192–196
 - summary of, 207–209
 - TEM (transverse electromagnetic) waves, 185
 - Mode conversion
 - cause of, 177
 - modeling, 200–201
 - at RPDs
 - microstrip-to-microstrip via transition, 217–222
 - plane bounce from return currents, 209–217
 - split planes, 222–226
 - terminated microstrip transmission lines, 214–217
 - unterminated microstrip transmission lines, 212–214
 - Modified nodal analysis (MNA). *See* MNA (modified nodal analysis).
 - MTL equations, 189–192
 - MTL (multiconductor transmission line) theory, 185–186
 - Multilayered finite-difference method (M-FDM). *See* M-FDM (multilayered finite-difference method).
 - Multiport networks
 - digital signals, spectrum, 454–457
 - introduction, 451–453
- ## N
- NMOS (n-channel) transistor, 2
 - Noise. *See also* SSN (simultaneous switching noise). core PDN
 - measurement, 336–337
 - model-to-hardware correlation, 337–340
 - system-level measurement, 340–345
 - coupling reduction with thin dielectrics, 231–233
 - I/O PDN
 - description, 345
 - model-to-hardware correlation, 345–346
 - system-level model and measurement, 346–349
 - simulation, 361–364
 - Noise, power/ground management
 - embedded planar capacitors
 - FSB (front-side bus), 405, 410–411
 - introduction, 404–405

- planar capacitors, 405–407
 - SSN, and jitter and voltage margin, 410–415
 - test vehicle, 407–410
 - integrating into IBM packages, 400–404
 - introduction, 392–394
 - purpose of, 395
 - thick-film capacitor arrays, designing, 395–400
 - thin- or thick-film capacitors, 394–395
- NOP capacitors, 36–37
- O**
- Ohm's law, 20
- On-chip decoupling capacitors, 43
- On-chip power distribution
- chip-package antiresonance, 43–44, 62–65
 - description, 42–43
 - gate-leakage current, 44–45
 - on-chip capacitors, 43
 - on-chip voltage islands, 45
- Oscillations, spurious, 305–307
- Output buffers, modeling, 180–184
- P**
- Package planes
- antiresonance frequencies, 41–42
 - considerations, 41–42
 - description, 37
 - electromagnetic resonant cavities, 38–40
 - impedance, 40–41
 - plane bounce, 40
 - plane pairs, 37–39
 - resonance, 39–40
 - resonance frequencies, 41–42
 - role of, 39
- Padé, Henri Eugene, 245
- Padé approximation, 245
- Parallel-plate mode
- application. *See* Dielectrics, extracting material properties.
 - configuring, 186–189
 - definition, 186
 - stripline configuration
 - alternate modeling method, 196–200
 - continuous reference planes without holes, 196–200
 - CPW (computer-backed coplanar waveguide), 205–207
 - CPW mode, 205–207
 - inhomogeneous medium, 201–205
 - modeling as an MTL, 192–196
 - MTL equations, 189–192
 - overview, 189
 - perforated reference plane with a hole, 200
- Passivity condition, 254–256
- Passivity enforcement
- BEMP (Broadband Efficient Macromodeling Program), 258–266
 - curve fitting, 257–258
 - Hamiltonian matrix method
 - admittance parameters, 272–273
 - complex conjugate poles, 270–272
 - IdEM (Identification of Electrical Macromodels), 282–283
 - impedance parameters, 272–273
 - overview, 266–272
 - perturbation of matrices, 274–283
 - real poles, 268–270
 - scattering parameters, 273–276
 - overview, 257–258
- PCB analysis. *See* High-speed differential signaling; High-speed server analysis; ICs (integrated circuits), package analysis.
- P-channel (PMOS) transistor, 2
- PDN (power delivery network)
- analyzing
 - distributed analysis, 55–60
 - examples, 49–52, 57–59
 - plane bounce, minimizing, 59–60
 - plane inductance, at low frequencies, 52–53
 - single-node analysis, 48–55
 - target impedance, at cavity resonance, 59–60
 - target impedance, below cavity resonance, 53–55
 - analyzing, frequency domain
 - cavity response, 53–55
 - distributed analysis, 55–60
 - introduction, 45–48
 - plane inductance, calculating at low frequencies, 52–56
 - single-node analysis, 48–55
 - target impedance, meeting, 53–55, 59–60
 - chip decoupling capacitance, 43–44
 - chip-package antiresonance
 - description, 43–44
 - example, 62–65
 - components
 - board planes, 37–42
 - bypass capacitors, 28–37
 - decoupling capacitors, 28–37
 - illustration, 25
 - on-chip capacitors, 43
 - on-chip power distribution, 42–45
 - package planes, 37–42
 - plane pairs, 37–42
 - voltage regulators. *See* VRMs (voltage regulator modules).
 - description, 6–8
 - designing, 20–24
 - effectiveness, measuring. *See* High-frequency measurements.
 - example, 7
 - impedance
 - calculating, 45–48
 - frequency domain, 45–48
 - and noise voltage, 22–24
 - role of PDN components, 47–48
 - self, 46–47, 68–69
 - signature of current excitation, 46
 - slew rate, 46
 - time domain, 46
 - transfer, 46, 70
 - maximum current draw, calculating, 20–21
 - modeling methodology overview, 77–79.
 - See also specific methods.*
 - nose signature, 9

- power supply fluctuations, causes of, 8–10
- supply voltage conversion, 25–28
- target impedance, 20–22
- transients, 8–10
- PEEC plane modeling method
 - description, 89–90
 - inductance and resistance matrices, extracting, 90–94
- Perforated power/ground plane, 198
- Performance factors, 5, 29–34
- Perturbation of Hamiltonian matrices, 274–283
- Per-unit-length (pul), 33
- Plane bounce
 - board planes, 40
 - SSN modeling, modal decomposition
 - definition, 185
 - perforated power/ground plane, 198
 - from return currents, 209–217
 - split planes, 223–226
 - via transitions, 220
- Plane modeling
 - analytical methods
 - cavity resonator, network representation, 135–138
 - cavity resonator method, 133–135
 - Green's function, 133–138
 - rectangular planes, 133–138
 - description, 83–84
 - high-speed differential signaling, 352–358
 - introduction, 83–84
 - lumped, partial inductances, 89–94. *See also* Plane modeling, distributed circuit-based.
 - master/slave islands, modeling, 358–360
 - multiple plane pairs
 - coupling through apertures, 158–169
 - coupling through conductors, 154–158
 - coupling through vias, 141–154
 - description, 138–141
 - M-FDM (multilayered finite-difference method), 159–169
 - PEEC method, 89–94
 - plane behavior
 - antiresonance, 86–88
 - capacitance, calculating, 85–86
 - frequency domain behavior, 84–86
 - inductance, calculating, 85–86
 - resonance, 86–88
 - standing wave resonance, 84
 - time domain behavior, 86–88
 - two-dimensional, 88–89
 - SSN (simultaneous switching noise). *See* SSN modeling, planes.
- Plane modeling, discretization-based
 - FDM (finite-difference method)
 - description, 117–123
 - discrete cosine transform, 126–128
 - five-point approximation, *versus* nine-point, 124–126
 - rapid solver for rectangular planes, 126–128
 - T-unit cell *versus* X-unit cell, 123–124
 - FDTD (finite-difference time-domain) method, 128–132
 - FEM (finite element method), 132–133
 - rectangular planes, rapid solver, 126–128
- Plane modeling, distributed circuit-based. *See also* Plane modeling, lumped.
 - frequency-dependent unit cell elements
 - conductor losses, 111–113
 - Debye model, 106–111
 - description, 104–106
 - Kramers–Kronig relationship, 106–111
 - loss tangents, calculating, 107–108
 - skin effect, 111–113
 - substrate losses, 106–111
 - gaps in planes, 113–117
 - TMM (transmission matrix method), 97–104
 - transmission lines, 94–97
- Plane pairs
 - board planes, 37–39
 - description, 83–84
 - multiple, modeling
 - coupling through apertures, 158–169
 - coupling through conductors, 154–158
 - coupling through vias, 141–154
 - description, 138–141
 - M-FDM (multilayered finite-difference method), 159–169
 - SSN modeling, 185
- Planes
 - behavior modeling. *See* Plane modeling.
 - board
 - antiresonance frequencies, 41–42
 - considerations, 41–42
 - description, 37
 - electromagnetic resonant cavities, 38–40
 - impedance, 40–41
 - plane bounce, 40
 - plane pairs, 37–39
 - resonance, 39–40
 - resonance frequencies, 41–42
 - role of, 39
 - continuous reference, without holes, 196–200
 - effectiveness, measuring. *See* High-frequency measurements.
 - frequency response calculation. *See* Plane modeling.
 - ground
 - inductance, 32–33
 - resonance, 39–40
 - interconnections, separating. *See* Modal decomposition.
 - modeling. *See* Plane modeling.
 - package
 - antiresonance frequencies, 41–42
 - considerations, 41–42
 - description, 37
 - electromagnetic resonant cavities, 38–40
 - impedance, 40–41
 - plane bounce, 40, 59–60
 - plane pairs, 37–39
 - resonance, 39–40
 - resonance frequencies, 41–42
 - role of, 39
 - perforated power/ground, 198
 - perforated reference plane with a hole, 200
 - power/ground, and signal lines. *See* SSN modeling.
 - split, 223–226
- PMOS (p-channel) transistor, 2
- Pole identification, 249–251

- Power, cosimulation, 312–317
- Power delivery, 4–6
- Power delivery network (PDN). *See* PDN (power delivery network).
- Power planes, resonance, 39–40
- Power/ground noise management
 - embedded planar capacitors
 - FSB (front-side bus), 405, 410–411
 - introduction, 404–405
 - planar capacitors, 405–407
 - SSN, and jitter and voltage margin, 410–415
 - test vehicle, 407–410
 - integrating into IBM packages, 400–404
 - introduction, 392–394
 - purpose of, 395
 - thick-film capacitor arrays, designing, 395–400
 - thin- or thick-film capacitors, 394–395
- Pul (per-unit-length), 33

- Q**
- Q (quality) factor, 35–36

- R**
- Radiated emissions, controlling, 28
- Rapid solver for rectangular planes, 126–128
- Rational function method
 - approximating functions, 245–246
 - disadvantages, 291–295
 - theory, 244–246
- Rational function method, time-domain simulation
 - approximating functions, 245–246
 - disadvantages, 291–295
 - integration in a circuit solver
 - convolution, 283–288
 - direct convolution, 285–287
 - recursive convolution, 287–288
 - Spice subcircuit, 288–291
 - interpolation schemes
 - eigenvalue method, 246–249
 - pole identification, 249–251
 - residue identification, 251
 - vector fitting method, 249–251
 - passivity enforcement
 - BEMP (Broadband Efficient Macromodeling Program), 258–266
 - curve fitting, 257–258
 - overview, 257–258
 - passivity enforcement, Hamiltonian matrix method
 - admittance parameters, 272–273
 - complex conjugate poles, 270–272
 - IdEM (Identification of Electrical Macromodels), 282–283
 - impedance parameters, 272–273
 - overview, 266–272
 - perturbation of matrices, 274–283
 - real poles, 268–270
 - scattering parameters, 273–276
 - rational functions, properties of
 - overview, 252–253
 - passivity condition, 254–256
 - stability condition, 253–254
 - theory, 244–246
- Rational functions
 - modeling, 361
 - properties of
 - overview, 252–253
 - passivity condition, 254–256
 - stability condition, 253–254
- Real poles, 268–270
- Rectangular planes
 - analytical modeling methods, 133–138
 - discretization-based methods, 126–128
 - rapid solver, 126–128
- Recursive convolution, 287–288
- Residue identification, 251
- Resistance matrices, extracting, 90–94
- Resonance
 - board planes, 39–42
 - planes, 86–88
- Return currents
 - embedded planar capacitors
 - FSB (front-side bus), 405, 410–411
 - introduction, 404–405
 - planar capacitors, 405–407
 - SSN, and jitter and voltage margin, 410–415
 - test vehicle, 407–410
 - integrating into IBM packages, 400–404
 - introduction, 392–394
 - purpose of, 395
 - thick-film capacitor arrays, designing, 395–400
 - thin- or thick-film capacitors, 394–395
- RF/digital integration, 434–436
- RPD (return-path discontinuity)
 - mode conversion
 - microstrip-to-microstrip via transition, 217–222
 - plane bounce from return currents, 209–217
 - split planes, 222–226
 - terminated microstrip transmission lines, 214–217
 - unterminated microstrip transmission lines, 212–214

- S**
- Scattering parameters, 273–276
- Second order effects
 - fringe fields, 424–427
 - gap fields, 427–430
- Self impedance
 - measuring, 68–69
 - PDN analysis, 46–47
- SFGs (signal flow graphs), time-domain simulation
 - all-pass functions, 299
 - causal, 302–303
 - causality, 296
 - computational aspects
 - FFT (fast Fourier transform), 304–305
 - Gibbs phenomenon, 305–307
 - inverse Z-transform, 304–305
 - Kaiser window, 305–307
 - overview, 303–304
 - spurious oscillations, 305–307
 - windowing, 305–307

- delay extraction from frequency response, 300–302
 - fast convolution methods, 307–312
 - minimum phase, 296–299
 - overview, 295–296
 - power, cosimulation, 312–317
 - signal, cosimulation, 312–317
 - transfer-function causality, 296
- Signal, cosimulation, 312–317
- Signal lines
 - coaxial cables, 72–73
 - and power/ground planes. *See* SSN modeling.
 - SSN
 - return path discontinuities, 75–76
 - transmission line parameters, 74–75
 - transmission line theory, 72–74
 - as transmission lines, 72–74
- Simultaneous switching noise (SSN). *See* SSN (simultaneous switching noise).
- Single-phase nonisolated buck converters, 25–28
- Skin effect, 111–113
- SMDs (surface mount devices), 29, 36–37
- Software tools
 - BEMP (Broadband Efficient Macromodeling Program), 258–266, 458
 - Sphinx-book, 458
- Sources (transistor), 2–3
- S-parameters, 322–327
- Sphinx-book, 458
- Spice subcircuit, 288–291
- Split planes, 223–226
- Spurious oscillations, 305–307
- SSN (simultaneous switching noise)
 - frequency domain analysis
 - microstrip-to-stripline via transition, 228–231
 - noise coupling reduction with thin dielectrics, 231–233
 - stripline, between power and ground plane, 226–228
 - I/O circuit delay, 15–16
 - jitter effects, 410–415
 - methods, 175–177
 - M-FDM, incorporating transmission lines
 - complex board design, 236–238
 - overview, 233–236
 - mode conversion at RPDs
 - microstrip-to-microstrip via transition, 217–222
 - plane bounce from return currents, 209–217
 - split planes, 222–226
 - terminated microstrip transmission lines, 214–217
 - unterminated microstrip transmission lines, 212–214
 - parasitics, 176–177
 - RPD (return-path discontinuity), 177
 - signal lines, 74–76
 - simple models
 - IBIS (I/O buffer information specification), 180–184
 - modeling output buffers, 180–184
 - overview, 177–180
 - time domain analysis
 - microstrip-to-microstrip via transition, 217–222
 - plane bounce from return currents, 209–217
 - RPD (return-path discontinuity), 217–222
 - split planes, 222–226
 - terminated microstrip transmission lines, 214–217
 - unterminated microstrip transmission lines, 212–214
 - timing margins, 16–17
 - voltage margins, 16–17, 410–415
- SSN modeling, modal decomposition. *See also* Time-domain simulation.
 - definition, 185–186
 - microstrip configuration, 186–189
 - MTL (multiconductor transmission line) theory, 185–186
 - overview, 185–186, 189
 - plane bounce
 - definition, 185
 - perforated power/ground plane, 198
 - from return currents, 209–217
 - split planes, 223–226
 - via transitions, 220
 - plane pairs, 185
 - stripline configuration
 - alternate modeling method, 196–200
 - continuous reference planes without holes, 196–200
 - CPW (computer-backed coplanar waveguide), 205–207
 - CPW mode, 205–207
 - inhomogeneous medium, 201–205
 - modeling as an MTL, 192–196
 - MTL equations, 189–192
 - overview, 189
 - parallel-plate mode, 205–207
 - perforated reference plane with a hole, 200
 - stripline, alternate modeling method, 196–200
 - stripline, modeling as an MTL, 192–196
 - summary of, 207–209
 - TEM (transverse electromagnetic) waves, 185
- SSN modeling, planes. *See also* Time-domain simulation.
 - microstrip configuration, 186–189
 - modal decomposition, 185–186
 - MTL (multiconductor transmission line) theory, 185–186
 - overview, 185–186, 189
 - plane bounce
 - definition, 185
 - perforated power/ground plane, 198
 - from return currents, 209–217
 - split planes, 223–226
 - via transitions, 220
 - plane pairs, 185
 - stripline configuration
 - alternate modeling method, 196–200
 - continuous reference planes without holes, 196–200
 - CPW (computer-backed coplanar waveguide), 205–207
 - CPW mode, 205–207
 - inhomogeneous medium, 201–205
 - MTL equations, 189–192
 - parallel-plate mode, 205–207
 - perforated reference plane with a hole, 200
 - stripline, modeling as an MTL, 192–196
 - summary of methods, 207–209
 - TEM (transverse electromagnetic) waves, 185

SSN modeling, transmission lines. *See also* Time-domain simulation.

- microstrip configuration, 186–189
- modal decomposition, 185–186
- MTL (multiconductor transmission line) theory, 185–186
- overview, 185–186, 189
- plane bounce
 - definition, 185
 - perforated power/ground plane, 198
 - from return currents, 209–217
 - split planes, 223–226
 - via transitions, 220
- plane pairs, 185
- stripline configuration
 - alternate modeling method, 196–200
 - continuous reference planes without holes, 196–200
 - CPW (computer-backed coplanar waveguide), 205–207
 - CPW mode, 205–207
 - inhomogeneous medium, 201–205
 - MTL equations, 189–192
 - parallel-plate mode, 205–207
 - perforated reference plane with a hole, 200
 - stripline, modeling as an MTL, 192–196
- summary of methods, 207–209
- TEM (transverse electromagnetic) waves, 185

Stability condition, 253–254

Standing wave resonance, 84

Stripline, between power and ground plane, 226–228

Stripline configuration

- alternate modeling method, 196–200
- continuous reference planes without holes, 196–200
- CPW (computer-backed coplanar waveguide), 205–207
- CPW mode, 205–207
- inhomogeneous medium, 201–205
- modeling as an MTL, 192–196
- MTL equations, 189–192
- overview, 189
- parallel-plate mode, 205–207
- perforated reference plane with a hole, 200

Substrate losses, 106–111

Surface mount devices (SMDs), 29, 36–37

T

TEM (transverse electromagnetic) waves, 185

Time-domain simulation. *See also* Modal decomposition.

- discretization-based plane models. *See* FDTD (finite-difference time-domain) method.
- microstrip-to-microstrip via transition, 217–222
- MNA (modified nodal analysis), 320–322
 - description, 317–318
 - frequency domain, 318–320
 - S-parameters, 322–327
 - time domain, 320–322
- PDN design, 20
- plane behavior, 86–88
- plane bounce from return currents, 209–217
- RPD (return-path discontinuity), 217–222
- split planes, 222–226

SSN modeling

- microstrip-to-microstrip via transition, 217–222
- plane bounce from return currents, 209–217
- RPD (return-path discontinuity), 217–222
- split planes, 222–226
- terminated microstrip transmission lines, 214–217
- unterminated microstrip transmission lines, 212–214
- terminated microstrip transmission lines, 214–217
- unterminated microstrip transmission lines, 212–214

Time-domain simulation, rational function method

- approximating functions, 245–246
- disadvantages, 291–295
- integration in a circuit solver
 - convolution, 283–288
 - direct convolution, 285–287
 - recursive convolution, 287–288
 - Spice subcircuit, 288–291
- interpolation schemes
 - eigenvalue method, 246–249
 - pole identification, 249–251
 - residue identification, 251
 - vector fitting method, 249–251
- passivity enforcement
 - BEMP (Broadband Efficient Macromodeling Program), 258–266
 - curve fitting, 257–258
 - overview, 257–258
- passivity enforcement, Hamiltonian matrix method
 - admittance parameters, 272–273
 - complex conjugate poles, 270–272
 - IdEM (Identification of Electrical Macromodels), 282–283
 - impedance parameters, 272–273
 - overview, 266–272
 - perturbation of matrices, 274–283
 - real poles, 268–270
 - scattering parameters, 273–276
- rational functions, properties of
 - overview, 252–253
 - passivity condition, 254–256
 - stability condition, 253–254
- theory, 244–246

Time-domain simulation, SFGs (signal flow graphs)

- all-pass functions, 299
- causal, 302–303
- causality, 296
- computational aspects
 - FFT (fast Fourier transform), 304–305
 - Gibbs phenomenon, 305–307
 - inverse Z-transform, 304–305
 - Kaiser window, 305–307
 - overview, 303–304
 - spurious oscillations, 305–307
 - windowing, 305–307
- delay extraction from frequency response, 300–302
- fast convolution methods, 307–312
- minimum phase, 296–299
- overview, 295–296
- power, cosimulation, 312–317
- signal, cosimulation, 312–317
- transfer-function causality, 296

- Time-varying current, 29–30
- Timing margins, SSN effects, 16–17
- TMM (transmission matrix method)
- combined with macromodeling. *See* High-speed differential signaling.
 - description, 97–104
 - for multiple planes
 - computing overall response, 149–151
 - decoupling capacitors, 149
 - description, 145–147
 - multilayered power/ground planes, with vias, 152–154
 - test structure, 151
 - vias and via coupling, 148–149
- Transfer impedance, 46, 70
- Transfer-function causality, 296
- Transistors. *See also* ICs (integrated circuits); Microprocessors.
- CMOS MOSFET technology, 1–3
 - drains, 2–3
 - function of, 1–3
 - gates, 2–3
 - inverters, 2–3
 - NMOS (n-channel), 2
 - PMOS (p-channel), 2
 - power delivery, 4–6
 - sources, 2–3
 - types of, 2
- Transmission line theory, 72–74
- Transmission lines
- matrix representation, 453–454
 - modeling, 94–97. *See also* SSN modeling, transmission lines.
 - signal lines as, 72–74
- Transverse electromagnetic (TEM) waves, 185
- Two-dimensional planes, 88–89
- V**
- Vector fitting method, 249–251
- Via transitions
- microstrip-to-microstrip, 217–222
 - microstrip-to-stripline, 228–231
 - plane bounce, 220
 - SSN modeling, 220
- Vias
- coupling, 141–154
 - multilayered power/ground planes, 152–154
- VNA (vector network analyzer)
- description, 65–66
 - measuring
 - impedance, 66–67, 336–337
 - impedance, by eliminating probe inductance, 70–71
 - self-impedance, 68–69
 - transfer impedance, 70
- Voltage margins, SSN effects, 16–17, 410–415
- Voltage planes, inductance, 32–33
- Voltage-frequency relationship, 5–7
- VRMs (voltage regulator modules)
- buck switching regulator, 26–27
 - bypassing. *See* Bypass capacitors; Decoupling capacitors.
 - conducted emissions, controlling, 28
 - control loop optimization, 28
 - DC-DC converters, 25–28
 - description, 24–26
 - design challenges, 27–28
 - efficiency, 27–28
 - four-element model, 26–27
 - illustration, 27
 - operating principle, 26
 - POL (point-of-load) converters. *See* DC-DC converters.
 - radiated emissions, controlling, 28
 - single-phase nonisolated buck converters, 25–28
- W**
- Wave propagation
- along signal lines. *See* Microstrip mode.
 - between power/ground planes. *See* Parallel-plate mode.
- Windowing, 305–307
- X**
- X5R capacitors, 36–37
- X7R capacitors, 36–37
- Y**
- Y5V capacitors, 36–37